Silicon P-Channel MOS FET

# HITACHI

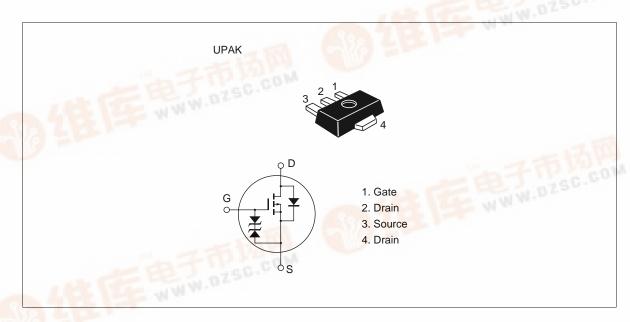
#### Application

High speed power switching

#### **Features**

- Low on-resistance
- High speed switching
- Low drive current
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

#### Outline





## Absolute Maximum Ratings ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	-200	V
Gate to source voltage	$V_{\sf GSS}$	±15	V
Drain current	I <sub>D</sub>	-0.5	А
Drain peak current	I <sub>D(pulse)</sub> *1	-1.0	А
Body to drain diode reverse drain current	I <sub>DR</sub>	-0.5	А
Channel dissipation	Pch*2	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

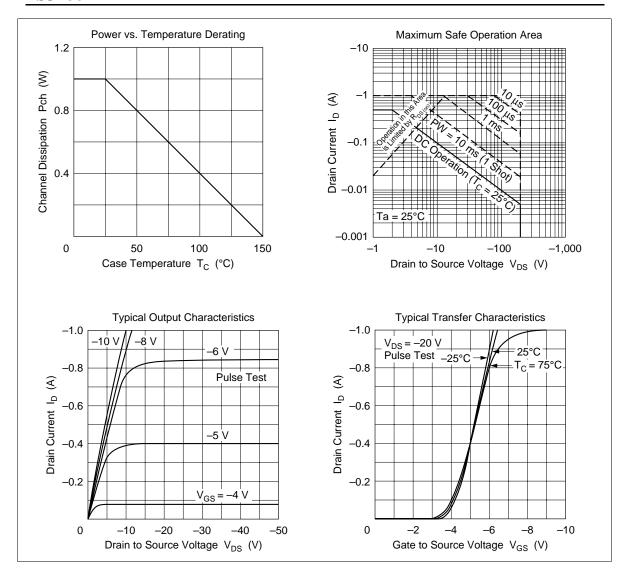
2. When using the alumina ceramic board (12.5×20×0.7 mm)

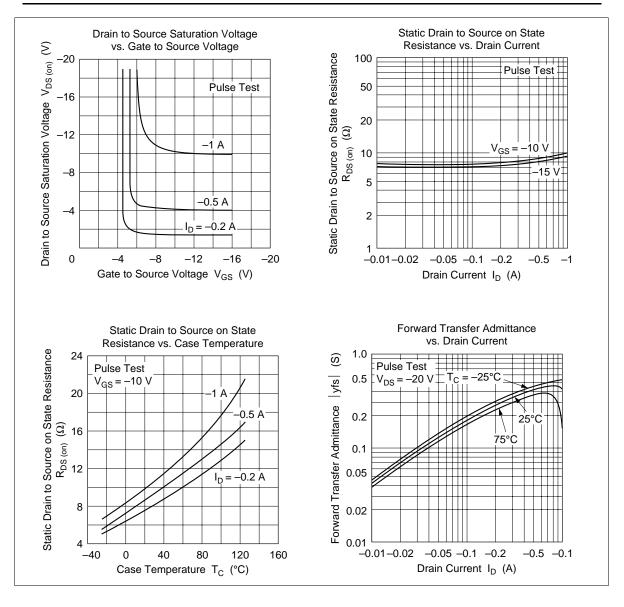
# **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

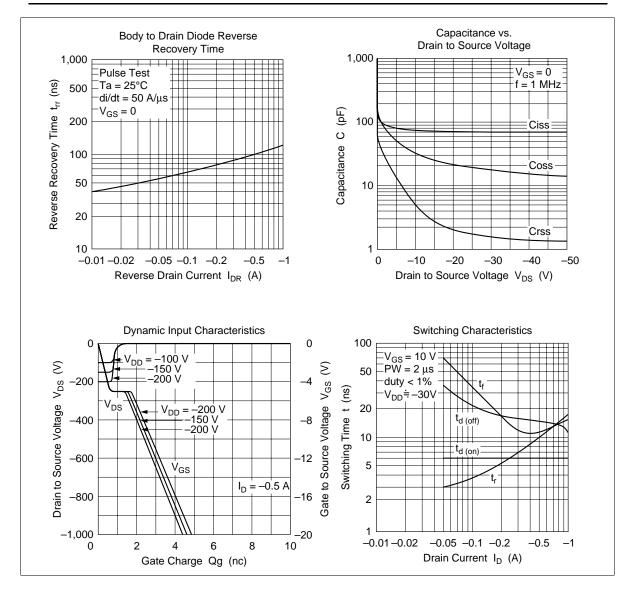
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-200	_	_	V	$I_{D} = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±15	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	-50	μΑ	$V_{DS} = -160 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	-2.0	_	-4.0	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Static drain to source on state	$R_{\scriptscriptstyle DS(on)}$	_	8.0	12.0	Ω	$I_D = -0.25 \text{ A}, V_{GS} = -10 \text{ V}^{*1}$
resistance		_	10.0	15.0		$I_D = -1 \text{ A}, V_{GS} = -10 \text{ V}^{*1}$
Forward transfer admittance	y <sub>fs</sub>	0.18	0.3	_	S	$I_D = -0.25 \text{ A}, V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	Ciss	_	75	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	32	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	5	_	pF	<del>-</del>
Turn-on delay time	t <sub>d(on)</sub>	_	6	_	ns	$I_D = -0.25 \text{ A}, V_{GS} = -10 \text{ V},$
Rise time	t <sub>r</sub>	_	6	_	ns	$R_L = 120 \Omega$
Turn-off delay time	$t_{\text{d(off)}}$	_	17	_	ns	<del>-</del>
Fall time	t <sub>f</sub>	_	15	_	ns	<del></del>
Body to drain diode forward voltage	$V_{DF}$		0.95		V	$I_F = -0.5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>	_	100		ns	$I_F = -0.5 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

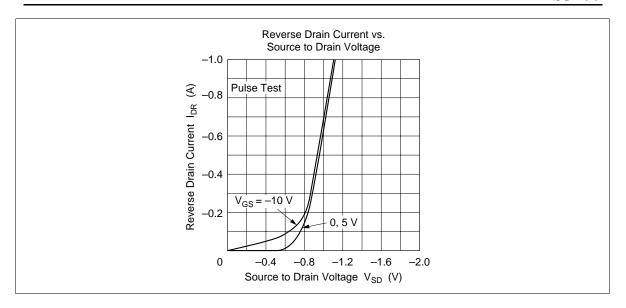
Note: 1. Pulse test

Marking for 2SJ186 is "CY".

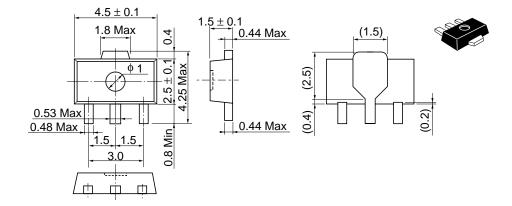








Unit: mm



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